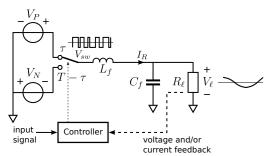
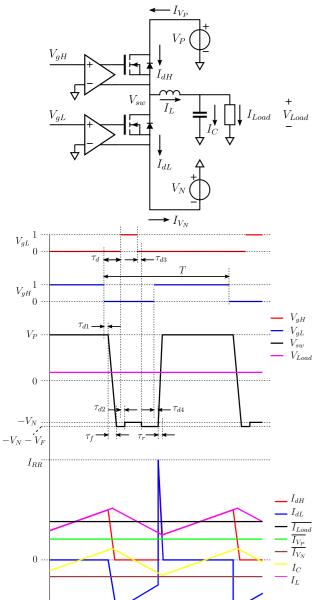
# Half-bridge operating principle



## Half-bridge switching behavior and power losses



Current delivered to the negative supply

TrenchFET<sup>®</sup> Gen IV power MOSFET

Tuned for the lowest R<sub>DS</sub> x Q<sub>oss</sub> FOM

100 % R<sub>a</sub> and UIS tested

Material categor compliance plea

**APPLICATIONS** 

Primary side switch

DC/DC converters

Motor drive control

Power supplies

Synchronous rectificat

Very low Ros x Qa figure-of-merit (FOM)

Si7454FDP Vishay Siliconix

(10)

RoHS COMPLIANT HALOGEN

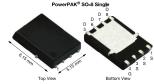
, **\_** 

N-Channel MOSFE

d s

# N-Channel 100 V (D-S) MOSFET

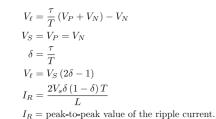
FEATURES



VISHAY.

Top View	Bottom View	
PRODUCT SUMMARY		
V <sub>DS</sub> (V)	100	
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 10 V	0.0295	
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 4.5 V	0.034	
Q <sub>g</sub> typ. (nC)	8	
D (A)	23.5	
Configuration	Single	

## **Output voltage and ripple current**



Expressions for peak ripple current much smaller than load current

# **MOS conduction losses**

 $P_{cM} \approx I_{load}^2 R_{dsOn} \frac{T - 2\tau_d}{T}$  $R_{dsOn} = MOS$  on resistance

# **Body diode conduction losses**

$P_{cD} \approx I_{load} V_F \frac{2\tau_d}{T}$	$V_F = \underset{\mbox{forward voltage at}}{\mbox{MOS body diode}} \\ \underset{\mbox{load current}}{\mbox{mod}}$	
Output charge losses		
$P_{oQ} \approx \frac{2}{T} Q_o \left( V_P + V_N \right)$	$\label{eq:Qo} Q_o = \underset{\text{charge}}{\text{MOS output}}$	
or		
$P_{oQ} \approx \frac{2}{T} C_o \left( V_P + V_N \right)^2$	$C_o = \underset{\text{capacitance}}{\text{MOS output}}$	

Reverse recovery losses

MOS body diode  $P_{RR} = \frac{1}{T} Q_{RR} \left( V_P + V_N \right)$  $Q_{RR}$ reverse recovery charge

# Switching losses

$$\begin{split} P_{sw} &= \frac{2}{T} \int_{0}^{\tau_{sw}} \left( V_P + V_N \right) \left( 1 - \frac{t}{\tau_{sw}} \right) I_{load} \frac{t}{\tau_{sw}} dt \\ &= \frac{\tau_{sw} I_{load} \left( V_N + V_P \right)}{3T} \\ \tau_{sw} &\approx \frac{C_{gd} \left( V_P + V_N \right)}{I_C} \\ \end{split}$$

Gate driver  $I_G =$ current

 $V_G = Gate driver$ 

 $C_{iss} =$ 

 $Q_G =$ charge

voltage

MOS input

MOS gate

capacitance

# **Gate driver losses**

 $P_G = \frac{1}{T} V_G^2 C_{iss}$ or

$$P_G = \frac{1}{T} V_G Q_G$$

Low losses and low EMI during quiescent operation: Resonant switching

MOS output  $I_R \tau_d \approx 2 \left( V_P + V_N \right) C_{oss}$ Core capacitance

FOM power devices: ine a low charge storage with a low on resistance.

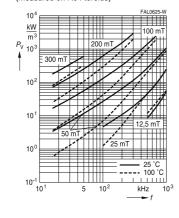
### **Core losses**

Manufacturer's calculation tools Material specification

SIFERRIT m



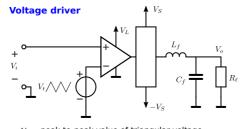
Relative core losses versus frequency (measured on R34 toroids)



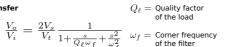


# Fixed frequency PWM

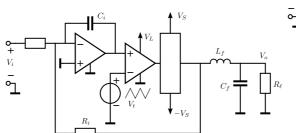
Transfe



# $V_t =$ peak-to-peak value of triangular voltage



Nonlinearity caused by: - dead zone - signal-dependent delay - signal-dependent rise and fall times Can be reduced through application of negative feedback



Small-signal bandwidth: firt-order LP product:  $B_f = \frac{2V_S}{2\pi V_t R_i C_i}$ Large-signal stability:  $f_{sw} > \pi B$  f Rate of change at the output of the integrator should not exceed that of the triangular signal

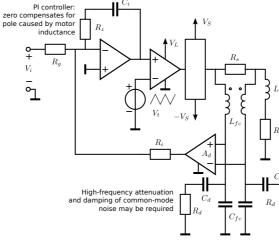
Further improvements (both methods require frequency compensation) Include output filter in the feedback loop

Include one more integrator in the feedback loop

### $S_{\tau} \left| \frac{s^2}{Hz} \right|$ Spectral density

Equivalent voltage noise density spectrum at the input of the comparator:  

$$S_{t} = S_{t} \frac{V_{t}^{2}}{2} \left[ \frac{V^{2}}{2} \right]$$



Compensation of the effect of a small cable capacitance requires two extra (complex) poles in the loop

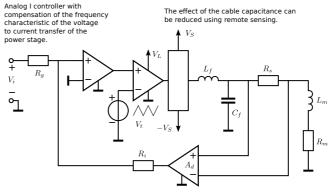
### With output filter

An output filter can be applied to: - Relax the CMRR requirements and/or CM filter requirements for the current

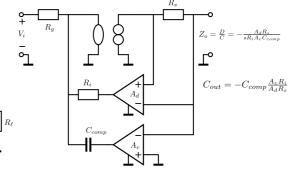
sense circuit Reduce the influence of high-frequency through the cable capacitance on

the transfer Reduce emission levels

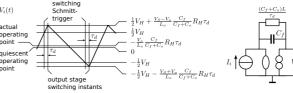
The output filter strongly complicates the design of the dynamic performance and the frequency stability of the current driver. An over sampling digital controller with integrated pulse width modulator may be a flexible and attractive alternative for an analog controller.



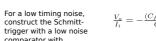
The effect of the cable capacitance and the motor capacitance can be reduced through application of capacitive voltage feedback at the load, thereby creating a negative output capacitance that compensates for the load capacitance.

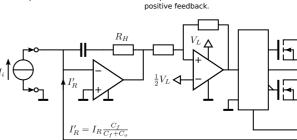


A finite delay limits the gain at low frequencies



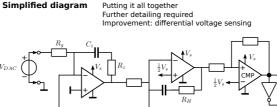
low-frequency gain can be compensated for by inserting a capacitor in series with

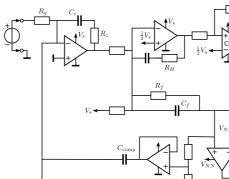




comparator with

# Hysteresis-based self-oscillating class D current driver





 $V_i(t)$ actua operating

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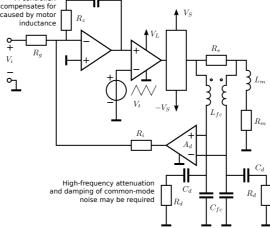
of timing noise in the MOS driver of the noise performance

Equivalent voltage noise density spectrum at the input of the com  

$$S_{t} = S_{t} V_{t}^{2} [V^{2}]$$

$$S_v=S_ au rac{V_s}{T^2} \left[rac{V_s^2}{ ext{Hz}}
ight]$$
 In isolated MOS / IGBT drivers: spurious frequency components may be present

# Without output filter

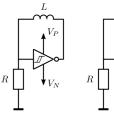


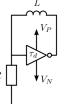


# **Fixed ripple current PWM**

### Hysteresis-based self-oscillating class D voltage driver

### First-order LR oscillators

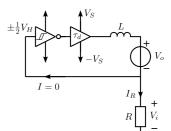




Comparator with

delav

Comparator with hvsteresis



Comparator with delay and hysteresis

## **Basic operation**

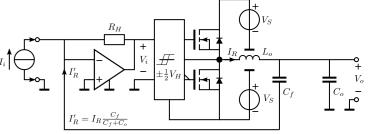
Schmitt-trigger switching levels:  $\pm \frac{1}{2}V_H$ 

Peak-to-peak value of the ripple current:

$$I_R = \frac{V_H}{R} + \frac{2V_S}{L}\tau_d$$
  
Oscillation frequency:  
$$f = \frac{1}{T} = \frac{1 - \frac{V_a^2}{V_S^2}}{\frac{2LV_H}{R_S} + 4\tau_d}$$

### Alternative configuration

Measure the ripple current through a large capacitor attenuate it and convert it into a voltage with a transimpedance amplifier



If the delay in the oscillator equals zero, the mean value of the voltage at the input is the output of the comparator does not depend on the signal and the circuit behaves as an ideal transimpedance integrator:  $\frac{V_{0}}{T_{0}} = -\frac{1}{T_{0}}$ 

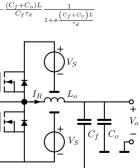
The output filter does not introduce

(observable) complex poles in this transfer.

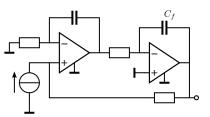
The DC transfer can be fixed accurately:

- Resistor in parallel with  $C_f$ - Extra feedback loop with non-inverting

integrator (with a zero) for lower distortion



11



First stage: extra loop integrator Second stage: Self oscillating class D transimpedance integartor (from figure above)

- PI controller with zero on motor time constant for setting the bandwidth

Fixed DC gain in power stage for adjusting the frequency response
 Low-noise current-sense amplifier as with over-all feedback class AB driver

Cable capacitance compensation

 Full-bridge amplifier by driving the MOS drivers of bothe halves with opposite phase
 Bandwidth, frequency response and cable capacitance compensation can be made adjustable with digitally-controlled potentiometers

### Fixed frequency versus fixed ripple current driver

### Fixed frequency

Discrete EMI components with relatively high amplitude at harmonics of the switching frequency

Rail to rail operation limited by minimum pulse width

High efficiency

Difficult to obtain a desired frequency response because the poles of the butput filter appear in the loop gain of the current control loop

### **Fixed ripple current**

Wide spectrum EMI with lower amplitude at unknown frequencies

Ripple voltage increases with voltage excursion Switching frequency drops below Nyquist at large voltage excursions

Higher efficiency because switching losses drop at large voltage excursions

Relatively easy to obtain a desired frequency response because the poles of the output filter do not appear in the loop gain of the current control loop.



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